# Catherine Bougerol

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

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|---|---|---|---|
| 274 papers | 7,905 citations | 47 h-index | 78 g-index |
| 293 ext. papers | 8,325 ext. citations | 3.9 avg, IF | 5.25 L-index |

| # | Paper | IF | Citations |
|---|---|---|---|
| 274 | Transport properties of a thin GaN channel formed in an Al0.9Ga0.1N/GaN heterostructure grown on AlN/sapphire template. *Journal of Applied Physics*, **2022**, 131, 124501 | 2.5 | 2 |
| 273 | The role of surface diffusion in the growth mechanism of III-nitride nanowires and nanotubes. *Nanotechnology*, **2021**, 32, 085606 | 3.4 | 2 |
| 272 | Dual-Color Emission from Monolithic m-Plane Core–Shell InGaN/GaN Quantum Wells. *Advanced Photonics Research*, **2021**, 2, 2000148 | 1.9 | 1 |
| 271 | Solubility Limit of Ge Dopants in AlGaN: A Chemical and Microstructural Investigation Down to the Nanoscale. *ACS Applied Materials & Interfaces*, **2021**, 13, 4165-4173 | 9.5 | 4 |
| 270 | Improvement of critical temperature of niobium nitride deposited on 8-inch silicon wafers thanks to an AlN buffer layer. *Superconductor Science and Technology*, **2021**, 34, 045002 | 3.1 | 1 |
| 269 | Comprehensive model toward optimization of SAG In-rich InGaN nanorods by hydride vapor phase epitaxy. *Nanotechnology*, **2021**, 32, 155601 | 3.4 | |
| 268 | Carrier dynamics near a crack in GaN microwires with AlGaN multiple quantum wells. *Applied Physics Letters*, **2020**, 117, 221105 | 3.4 | 4 |
| 267 | Controlling the shape of a tapered nanowire: lessons from the Burton-Cabrera-Frank model. *Nanotechnology*, **2020**, 31, 274004 | 3.4 | 0 |
| 266 | Role of Underlayer for Efficient Core-Shell InGaN QWs Grown on -plane GaN Wire Sidewalls. *ACS Applied Materials & Interfaces*, **2020**, 12, 19092-19101 | 9.5 | 12 |
| 265 | Formation of voids in selective area growth of InN nanorods in SiNx on GaN templates. *Nano Futures*, **2020**, 4, 025002 | 3.6 | 4 |
| 264 | Three-dimensional measurement of Mg dopant distribution and electrical activity in GaN by correlative atom probe tomography and off-axis electron holography. *Journal of Applied Physics*, **2020**, 127, 065702 | 2.5 | 7 |
| 263 | Internal quantum efficiency of AlGaN/AlN quantum dot superlattices for electron-pumped ultraviolet sources. *Nanotechnology*, **2020**, 31, 505205 | 3.4 | 3 |
| 262 | Optical and structural analysis of ultra-long GaAs nanowires after nitrogen-plasma passivation. *Nano Express*, **2020**, 1, 020019 | 2 | 2 |
| 261 | UV Emission from GaN Wires with -Plane Core-Shell GaN/AlGaN Multiple Quantum Wells. *ACS Applied Materials & Interfaces*, **2020**, 12, 44007-44016 | 9.5 | 7 |
| 260 | Correlative investigation of Mg doping in GaN layers grown at different temperatures by atom probe tomography and off-axis electron holography. *Nanotechnology*, **2020**, 31, 045702 | 3.4 | 6 |
| 259 | Si Doping of Vapor-Liquid-Solid GaAs Nanowires: n-Type or p-Type?. *Nano Letters*, **2019**, 19, 4498-4504 | 11.5 | 17 |
| 258 | Design and implementation of bound-to-quasibound GaN/AlGaN photovoltaic quantum well infrared photodetectors operating in the short wavelength infrared range at room temperature. *Journal of Applied Physics*, **2019**, 125, 174505 | 2.5 | 6 |

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| 257 | Selective growth of ordered hexagonal InN nanorods. *CrystEngComm*, **2019**, 21, 2702-2708 | 3.3 | 9 |
| 256 | High Lateral Breakdown Voltage in Thin Channel AlGaN/GaN High Electron Mobility Transistors on AlN/Sapphire Templates. *Micromachines*, **2019**, 10, | 3.3 | 16 |
| 255 | Improvement of the critical temperature of NbTiN films on III-nitride substrates. *Superconductor Science and Technology*, **2019**, 32, 035008 | 3.1 | 4 |
| 254 | Compositional control of homogeneous InGaN nanowires with the In content up to 90. *Nanotechnology*, **2019**, 30, 044001 | 3.4 | 6 |
| 253 | Dopant radial inhomogeneity in Mg-doped GaN nanowires. *Nanotechnology*, **2018**, 29, 255706 | 3.4 | 17 |
| 252 | High spatial resolution correlated investigation of Zn segregation to stacking faults in ZnTe/CdSe nanostructures. *Applied Physics Letters*, **2018**, 112, 093102 | 3.4 | 3 |
| 251 | Influence of Silicon on the Nucleation Rate of GaAs Nanowires on Silicon Substrates. *Journal of Physical Chemistry C*, **2018**, 122, 19230-19235 | 3.8 | 11 |
| 250 | Near-UV narrow bandwidth optical gain in lattice-matched III□itride waveguides. *Japanese Journal of Applied Physics*, **2018**, 57, 090305 | 1.4 | 1 |
| 249 | Green Electroluminescence from Radial m-Plane InGaN Quantum Wells Grown on GaN Wire Sidewalls by Metal□Organic Vapor Phase Epitaxy. *ACS Photonics*, **2018**, 5, 4330-4337 | 6.3 | 18 |
| 248 | Circumventing the miscibility gap in InGaN nanowires emitting from blue to red. *Nanotechnology*, **2018**, 29, 465602 | 3.4 | 13 |
| 247 | Self-catalyzed GaAs nanowires on silicon by hydride vapor phase epitaxy. *Nanotechnology*, **2017**, 28, 125602 | 3.4 | 11 |
| 246 | Thin-Wall GaN/InAlN Multiple Quantum Well Tubes. *Nano Letters*, **2017**, 17, 3347-3355 | 11.5 | 9 |
| 245 | Effect of Al incorporation in nonpolar m-plane GaN/AlGaN multi-quantum-wells using plasma-assisted molecular-beam epitaxy. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1600849 | 1.6 | 6 |
| 244 | Effect of Ge-doping on the short-wave, mid- and far-infrared intersubband transitions in GaN/AlGaN heterostructures. *Semiconductor Science and Technology*, **2017**, 32, 125002 | 1.8 | 6 |
| 243 | Spontaneous formation of GaN/AlN core□shell nanowires on sapphire by hydride vapor phase epitaxy. *Journal of Crystal Growth*, **2016**, 454, 1-5 | 1.6 | 3 |
| 242 | Self-catalyzed growth of GaAs nanowires on silicon by HVPE **2016**, | | 1 |
| 241 | Composition Analysis of III-Nitrides at the Nanometer Scale: Comparison of Energy Dispersive X-ray Spectroscopy and Atom Probe Tomography. *Nanoscale Research Letters*, **2016**, 11, 461 | 5 | 15 |
| 240 | Chemical composition fluctuations and strain relaxation in InGaN nanowires: The role of the metal/nitrogen flux ratio. *Materials Science in Semiconductor Processing*, **2016**, 55, 79-84 | 4.3 | 7 |

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| 239 | Interfacial chemistry in a ZnTe/CdSe superlattice studied by atom probe tomography and transmission electron microscopy strain measurements. *Journal of Microscopy*, **2016**, 262, 178-82 | 1.9 | 8 |
| 238 | Flexible White Light Emitting Diodes Based on Nitride Nanowires and Nanophosphors. *ACS Photonics*, **2016**, 3, 597-603 | 6.3 | 72 |
| 237 | Effect of doping on the far-infrared intersubband transitions in nonpolar m-plane GaN/AlGaN heterostructures. *Nanotechnology*, **2016**, 27, 145201 | 3.4 | 11 |
| 236 | Short-wavelength, mid- and far-infrared intersubband absorption in nonpolar GaN/Al(Ga)N heterostructures. *Japanese Journal of Applied Physics*, **2016**, 55, 05FG05 | 1.4 | 7 |
| 235 | Dependence of the photovoltaic performance of pseudomorphic InGaN/GaN multiple-quantum-well solar cells on the active region thickness. *Applied Physics Letters*, **2016**, 108, 161907 | 3.4 | 16 |
| 234 | GaN Rods Grown on Si by SAG-HVPE toward GaN HVPE/InGaN MOVPE Core/Shell Structures. *Crystal Growth and Design*, **2016**, 16, 2509-2513 | 3.5 | 7 |
| 233 | InGaN nanowires with high InN molar fraction: growth, structural and optical properties. *Nanotechnology*, **2016**, 27, 195704 | 3.4 | 14 |
| 232 | Flexible Photodiodes Based on Nitride Core/Shell p-n Junction Nanowires. *ACS Applied Materials & Interfaces*, **2016**, 8, 26198-26206 | 9.5 | 52 |
| 231 | Atomic arrangement at ZnTe/CdSe interfaces determined by high resolution scanning transmission electron microscopy and atom probe tomography. *Applied Physics Letters*, **2015**, 106, 051904 | 3.4 | 14 |
| 230 | Investigation of Photovoltaic Properties of Single Core-Shell GaN/InGaN Wires. *ACS Applied Materials & Interfaces*, **2015**, 7, 21898-906 | 9.5 | 32 |
| 229 | Intersubband transitions in nonpolar GaN/Al(Ga)N heterostructures in the short- and mid-wavelength infrared regions. *Journal of Applied Physics*, **2015**, 118, 014309 | 2.5 | 24 |
| 228 | Flexible Light-Emitting Diodes Based on Vertical Nitride Nanowires. *Nano Letters*, **2015**, 15, 6958-64 | 11.5 | 149 |
| 227 | The influence of AlN buffer over the polarity and the nucleation of self-organized GaN nanowires. *Journal of Applied Physics*, **2015**, 117, 245303 | 2.5 | 49 |
| 226 | Nonpolar m-plane GaN/AlGaN heterostructures with intersubband transitions in the 5-10 THz band. *Nanotechnology*, **2015**, 26, 435201 | 3.4 | 23 |
| 225 | THz intersubband transitions in AlGaN/GaN multi-quantum-wells. *Physica Status Solidi (A) Applications and Materials Science*, **2014**, 211, 761-764 | 1.6 | 9 |
| 224 | M-Plane GaN/InAlN Multiple Quantum Wells in Core–Shell Wire Structure for UV Emission. *ACS Photonics*, **2014**, 1, 38-46 | 6.3 | 37 |
| 223 | Cu2ZnSn(S1−xSex)4 thin films for photovoltaic applications: Influence of the precursor stacking order on the selenization process. *Journal of Alloys and Compounds*, **2014**, 588, 310-315 | 5.7 | 18 |
| 222 | Pseudo-square AlGaN/GaN quantum wells for terahertz absorption. *Applied Physics Letters*, **2014**, 105, 131106 | 3.4 | 23 |

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| 221 | Ultralong and defect-free GaN nanowires grown by the HVPE process. *Nano Letters*, **2014**, 14, 559-62 | 11.5 | 50 |
| 220 | Improved conversion efficiency of as-grown InGaN/GaN quantum-well solar cells for hybrid integration. *Applied Physics Express*, **2014**, 7, 032301 | 2.4 | 17 |
| 219 | High-quality NbN nanofilms on a GaN/AlN heterostructure. *AIP Advances*, **2014**, 4, 107123 | 1.5 | 7 |
| 218 | High-Tc Superconducting Cuprates, (Ce,Y)sO2s-2Sr2(Cu2.75Mo0.25)O6+□Tc-increase with apical Cu-O decrease at constant Cu-O planar distance. *Journal of Physics: Conference Series*, **2014**, 507, 012031 | 0.3 | 1 |
| 217 | Effect of the quantum well thickness on the performance of InGaN photovoltaic cells. *Applied Physics Letters*, **2014**, 105, 131105 | 3.4 | 47 |
| 216 | Metal organic vapour-phase epitaxy growth of GaN wires on Si (111) for light-emitting diode applications. *Nanoscale Research Letters*, **2013**, 8, 61 | 5 | 25 |
| 215 | Optical properties of single ZnTe nanowires grown at low temperature. *Applied Physics Letters*, **2013**, 103, 222106 | 3.4 | 17 |
| 214 | Strain assisted inter-diffusion in GaN/AlN quantum dots. *Journal of Applied Physics*, **2013**, 113, 034311 | 2.5 | 14 |
| 213 | Growth of II□VI ZnSe/CdSe nanowires for quantum dot luminescence. *Journal of Crystal Growth*, **2013**, 378, 233-237 | 1.6 | 7 |
| 212 | Growth, structural and optical properties of AlGaN nanowires in the whole composition range. *Nanotechnology*, **2013**, 24, 115704 | 3.4 | 56 |
| 211 | InGaN/GaN multiple-quantum well heterostructures for solar cells grown by MOVPE: case studies. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 350-354 | | 6 |
| 210 | Intrinsic limits governing MBE growth of Ga-assisted GaAs nanowires on Si(111). *Journal of Crystal Growth*, **2013**, 364, 118-122 | 1.6 | 22 |
| 209 | Probing alloy composition gradient and nanometer-scale carrier localization in single AlGaN nanowires by nanocathodoluminescence. *Nanotechnology*, **2013**, 24, 305703 | 3.4 | 22 |
| 208 | Overdoped cuprates with high-temperature superconducting transitions. *APL Materials*, **2013**, 1, 021103 | 5.7 | 11 |
| 207 | Terahertz absorbing AlGaN/GaN multi-quantum-wells: Demonstration of a robust 4-layer design. *Applied Physics Letters*, **2013**, 103, 091108 | 3.4 | 25 |
| 206 | Structural and optical properties of Alx Ga1□N nanowires. *Physica Status Solidi - Rapid Research Letters*, **2013**, 7, 868-873 | 2.5 | 32 |
| 205 | Photovoltaic Response of InGaN/GaN Multiple-Quantum Well Solar Cells. *Japanese Journal of Applied Physics*, **2013**, 52, 08JH05 | 1.4 | 21 |
| 204 | Advanced semiconductor characterization with aberration corrected electron microscopes. *Journal of Physics: Conference Series*, **2013**, 471, 012001 | 0.3 | 3 |

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| 203 | Growth, structural and optical properties of GaN/AlN and GaN/GaInN nanowire heterostructures. *Physics Procedia*, **2012**, 28, 5-16 | | 3 |
| 202 | Growth mechanism and properties of InGaN insertions in GaN nanowires. *Nanotechnology*, **2012**, 23, 135703 | 3.4 | 63 |
| 201 | In situ study of self-assembled GaN nanowires nucleation on Si(111) by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2012**, 100, 212107 | 3.4 | 44 |
| 200 | Exciton-phonon coupling efficiency in CdSe quantum dots embedded in ZnSe nanowires. *Physical Review B*, **2012**, 85, | 3.3 | 9 |
| 199 | Extraction of the homogeneous linewidth of the spectrally diffusing line of a CdSe/ZnSe quantum dot embedded in a nanowire. *Physical Review B*, **2012**, 86, | 3.3 | 6 |
| 198 | Ultrafast room temperature single-photon source from nanowire-quantum dots. *Nano Letters*, **2012**, 12, 2977-81 | 11.5 | 58 |
| 197 | Paramagnetic shift in thermally annealed CdxZn1−xSe quantum dots. *New Journal of Physics*, **2012**, 14, 043038 | 2.9 | 9 |
| 196 | Catalyst-assisted hydride vapor phase epitaxy of GaN nanowires: exceptional length and constant rod-like shape capability. *Nanotechnology*, **2012**, 23, 405601 | 3.4 | 28 |
| 195 | Nordgauite, MnAl2(PO4)2(F,OH)2·5H2O, a new mineral from the Hagendorf-Süd pegmatite, Bavaria, Germany: description and crystal structure. *Mineralogical Magazine*, **2011**, 75, 269-278 | 1.7 | 12 |
| 194 | Subnanosecond spectral diffusion of a single quantum dot in a nanowire. *Physical Review B*, **2011**, 84, | 3.3 | 41 |
| 193 | Nucleation of GaN nanowires grown by plasma-assisted molecular beam epitaxy: The effect of temperature. *Journal of Crystal Growth*, **2011**, 334, 177-180 | 1.6 | 45 |
| 192 | Towards vertical coupling of CdTe/ZnTe quantum dots formed by a high temperature tellurium induced process. *Journal of Crystal Growth*, **2011**, 335, 28-30 | 1.6 | 22 |
| 191 | Polarity of GaN nanowires grown by plasma-assisted molecular beam epitaxy on Si(111). *Physical Review B*, **2011**, 84, | 3.3 | 89 |
| 190 | Polarity determination in ZnSe nanowires by HAADF STEM. *Journal of Physics: Conference Series*, **2011**, 326, 012044 | 0.3 | 4 |
| 189 | Measuring two dimensional strain state of AlN quantum dots in GaN nanowires by nanobeam electron diffraction. *Journal of Physics: Conference Series*, **2011**, 326, 012047 | 0.3 | 3 |
| 188 | Insertion of CdSe quantum dots in ZnSe nanowires: MBE growth and microstructure analysis. *Journal of Crystal Growth*, **2011**, 323, 330-333 | 1.6 | 4 |
| 187 | Catalyst-free growth of high-optical quality GaN nanowires by metal-organic vapor phase epitaxy. *Applied Physics Letters*, **2011**, 99, 251910 | 3.4 | 36 |
| 186 | M-plane core-shell InGaN/GaN multiple-quantum-wells on GaN wires for electroluminescent devices. *Nano Letters*, **2011**, 11, 4839-45 | 11.5 | 172 |

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|---|---|---|---|
| 185 | Insertion of CdSe quantum dots in ZnSe nanowires: Correlation of structural and chemical characterization with photoluminescence. *Journal of Applied Physics*, **2011**, 110, 034318 | 2.5 | 8 |
| 184 | Structural and optical properties of InGaN/GaN nanowire heterostructures grown by PA-MBE. *Nanotechnology*, **2011**, 22, 075601 | 3.4 | 92 |
| 183 | Subnanosecond spectral diffusion measurement using photon correlation. *Nature Photonics*, **2010**, 4, 696-699 | 33.9 | 105 |
| 182 | Optical spectroscopy of cubic GaN in nanowires. *Applied Physics Letters*, **2010**, 97, 081910 | 3.4 | 17 |
| 181 | Reversed polarized emission in highly strained a-plane GaN/AlN multiple quantum wells. *Physical Review B*, **2010**, 82, | 3.3 | 7 |
| 180 | Characterization of spin-state tuning in thermally annealed semiconductor quantum dots. *Physical Review B*, **2010**, 82, | 3.3 | 12 |
| 179 | Quantum transport in GaN/AlN double-barrier heterostructure nanowires. *Nano Letters*, **2010**, 10, 3545-50 | 12.5 | 68 |
| 178 | Ordering of Pd(2+) and Pd(4+) in the mixed-valent palladate KPd(2)O(3). *Inorganic Chemistry*, **2010**, 49, 1295-7 | 5.1 | 15 |
| 177 | The structural properties of GaN/AlN core-shell nanocolumn heterostructures. *Nanotechnology*, **2010**, 21, 415702 | 3.4 | 67 |
| 176 | Coulsellite, CaNa3AlMg3F14, a rhombohedral pyrochlore with 1:3 ordering in both A and B sites, from the Cleveland Mine, Tasmania, Australia. *American Mineralogist*, **2010**, 95, 736-740 | 2.9 | 7 |
| 175 | Molecular beam epitaxy growth and optical properties of AlN nanowires. *Applied Physics Letters*, **2010**, 96, 061912 | 3.4 | 45 |
| 174 | Structural properties of GaN nanowires and GaN/AlN insertions grown by molecular beam epitaxy. *Journal of Physics: Conference Series*, **2010**, 209, 012010 | 0.3 | 5 |
| 173 | Elastic strain relaxation in GaN/AlN nanowire superlattice. *Physical Review B*, **2010**, 81, | 3.3 | 41 |
| 172 | Influence of thermal annealing on the structural and optical properties of GaN/AlN quantum dots. *Physica Status Solidi (B): Basic Research*, **2010**, 247, 1675-1678 | 1.3 | 5 |
| 171 | Epitaxial growth of ZnSe and ZnSe/CdSe nanowires on ZnSe. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 1526-1529 | | 11 |
| 170 | Growth mechanism of catalyst-free [0001] GaN and AlN nanowires on Si by molecular beam epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2246-2248 | | 6 |
| 169 | Quantum dot to quantum wire transition of m-plane GaN islands. *Physical Review B*, **2009**, 79, | 3.3 | 3 |
| 168 | GaN/AlGaN intersubband optoelectronic devices. *New Journal of Physics*, **2009**, 11, 125023 | 2.9 | 71 |

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| 167 | The structural properties of GaN insertions in GaN/AlN nanocolumn heterostructures. *Nanotechnology*, **2009**, 20, 295706 | 3.4 | 20 |
| 166 | Midinfrared intersubband absorption in GaN/AlGaN superlattices on Si(111) templates. *Applied Physics Letters*, **2009**, 95, 141911 | 3.4 | 41 |
| 165 | CdSe quantum dot in a ZnSe nanowire as an efficient source of single photons. *Physica Status Solidi (B): Basic Research*, **2009**, 246, 846-849 | 1.3 | |
| 164 | Type-II excitons in ZnTe/ZnSe quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 857-859 | | 4 |
| 163 | Strain effects in GaN/AlN short-period superlattices for intersubband optoelectronics. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S549-S552 | | 5 |
| 162 | Elaboration and optical properties of type-II ZnTe on ZnSe heterostructures. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2009**, 165, 85-87 | 3.1 | 3 |
| 161 | Type-II ZnTe/ZnSe quantum dots and quantum wells. *Superlattices and Microstructures*, **2009**, 46, 253-257 | 2.8 | 6 |
| 160 | Bright CdSe quantum dot inserted in single ZnSe nanowires. *Microelectronics Journal*, **2009**, 40, 253-255 | 1.8 | 2 |
| 159 | CdSe quantum dots in ZnSe nanowires as efficient source for single photons up to 220 K. *Journal of Crystal Growth*, **2009**, 311, 2123-2127 | 1.6 | 7 |
| 158 | Growth and properties of defect-free ZnSe nanowires and nanoneedles. *Physica Status Solidi (B): Basic Research*, **2009**, 246, 812-815 | 1.3 | 3 |
| 157 | Exciton dynamics of a single quantum dot embedded in a nanowire. *Physical Review B*, **2009**, 80, | 3.3 | 39 |
| 156 | Evidence for quantum-confined Stark effect in GaN/AlN quantum dots in nanowires. *Physical Review B*, **2009**, 80, | 3.3 | 87 |
| 155 | Strain relaxation in short-period polar GaN/AlN superlattices. *Journal of Applied Physics*, **2009**, 106, 013526 | 2.5 | 50 |
| 154 | Nucleation mechanism of GaN nanowires grown on (111) Si by molecular beam epitaxy. *Nanotechnology*, **2009**, 20, 415602 | 3.4 | 78 |
| 153 | Near infrared quantum cascade detector in GaN/AlGaN/AlN heterostructures. *Applied Physics Letters* , **2008**, 92, 011112 | 3.4 | 91 |
| 152 | High-speed operation of GaN/AlGaN quantum cascade detectors at 1.55 μm. *Applied Physics Letters*, **2008**, 93, 193509 | 3.4 | 43 |
| 151 | Defect-free ZnSe nanowire and nanoneedle nanostructures. *Applied Physics Letters*, **2008**, 93, 143106 | 3.4 | 32 |
| 150 | Negative magnetopolarization in thermally annealed self-assembled quantum dots. *Physical Review B*, **2008**, 77, | 3.3 | 11 |

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| 149 | Anisotropic strain state of the [11□00] GaN quantum dots and quantum wires. *Journal of Applied Physics*, **2008**, 104, 063521 | 2.5 | 3 |
| 148 | Optical properties of m-plane GaN quantum dots and quantum wires. *Journal of Applied Physics*, **2008**, 104, 103528 | 2.5 | 14 |
| 147 | Measuring local lattice polarity in AlN and GaN by high resolution Z-contrast imaging: The case of (0001) and (11□00) GaN quantum dots. *Applied Physics Letters*, **2008**, 92, 201904 | 3.4 | 17 |
| 146 | New germanates RCrGeO5 (R=Nd□Er, Y): Synthesis, structure, and properties. *Journal of Solid State Chemistry*, **2008**, 181, 2433-2441 | 3.3 | 7 |
| 145 | A high-temperature single-photon source from nanowire quantum dots. *Nano Letters*, **2008**, 8, 4326-9 | 11.5 | 96 |
| 144 | Exciton and biexciton luminescence from single GaN/AlN quantum dots in nanowires. *Nano Letters*, **2008**, 8, 2092-6 | 11.5 | 86 |
| 143 | CdSe quantum dot formation induced by amorphous Se. *Surface Science*, **2007**, 601, 2664-2666 | 1.8 | |
| 142 | Structural and optical properties of CdSe quantum dots induced by amorphous Se. *Journal of Crystal Growth*, **2007**, 301-302, 281-284 | 1.6 | 3 |
| 141 | Chemical twinning of the pyrochlore structure in the system Bi2O3□Fe2O3□Nb2O5. *Journal of Solid State Chemistry*, **2007**, 180, 158-166 | 3.3 | 9 |
| 140 | CdSe quantum dot formation: alternative paths to relaxation of a strained CdSe layer and influence of the capping conditions. *Nanotechnology*, **2007**, 18, 265701 | 3.4 | 9 |
| 139 | Anisotropic strain relaxation in a-plane GaN quantum dots. *Journal of Applied Physics*, **2007**, 101, 063541 | 2.5 | 21 |
| 138 | Self-assembly of CdSe□ZnSe(001) quantum dot structures mediated by a tellurium cap layer. *Applied Physics Letters*, **2007**, 91, 153110 | 3.4 | 7 |
| 137 | Growth of m-plane GaN quantum wires and quantum dots on m-plane 6H-SiC. *Journal of Applied Physics*, **2007**, 102, 074913 | 2.5 | 18 |
| 136 | Spin ladder compound Pb0.55Cd0.45V2O5: Synthesis and investigation. *Physical Review B*, **2007**, 76, | 3.3 | 1 |
| 135 | Anisotropic morphology of nonpolar a-plane GaN quantum dots and quantum wells. *Journal of Applied Physics*, **2007**, 102, 074304 | 2.5 | 35 |
| 134 | PITTONGITE, A NEW TUNGSTATE WITH A MIXED-LAYER, PYROCHLORE HEXAGONAL TUNGSTEN BRONZE STRUCTURE, FROM VICTORIA, AUSTRALIA. *Canadian Mineralogist*, **2007**, 45, 857-864 | 0.7 | 6 |
| 133 | Elastic and surface energies: Two key parameters for CdSe quantum dot formation. *Applied Physics Letters*, **2006**, 88, 233103 | 3.4 | 26 |
| 132 | Inserting one single Mn ion into a quantum dot. *Applied Physics Letters*, **2006**, 89, 193109 | 3.4 | 41 |

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| 131 | Morphology of CdSe/ZnSe quantum dots grown by MBE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 938-941 | | 6 |
| 130 | Tuning the magnetic properties of ZnCdSe/ZnSe quantum dots by thermal annealing. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 3904-3907 | | |
| 129 | Inserting one single Mn ion into a quantum dot. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 3992-3996 | | 4 |
| 128 | Control of single spins in individual magnetic quantum dots. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 3709-3718 | 1.3 | 4 |
| 127 | Unit-cell intergrowth of pyrochlore and hexagonal tungsten bronze structures in secondary tungsten minerals. *Journal of Solid State Chemistry*, **2006**, 179, 3860-3869 | 3.3 | 16 |
| 126 | Synthesis and structure investigation of the Pb3V(PO4)3 eulytite. *Journal of Solid State Chemistry*, **2005**, 178, 3715-3721 | 3.3 | 18 |
| 125 | Structure of LaCuO2.66: an oxidized delafossite compound containing hole-doped kagome planes of Cu2+ cations. *Solid State Sciences*, **2003**, 5, 1095-1104 | 3.4 | 23 |
| 124 | Fe and Co Nanowires and Nanotubes Synthesized by Template Electrodeposition. *Journal of the Electrochemical Society*, **2003**, 150, E468 | 3.9 | 35 |
| 123 | Surface quality studies of high-Tc superconductors of the Hg-, Tl- and HgxTl1-x-families: RBS and resonant C and O backscattering studies. *Nuclear Instruments & Methods in Physics Research B*, **2002**, 190, 673-678 | 1.2 | 1 |
| 122 | The superconducting bismuth-based mixed oxides. *Current Applied Physics*, **2002**, 2, 425-430 | 2.6 | 3 |
| 121 | PbMnO2.75 high-pressure phase having a new type of crystallographic shear structure derived from perovskite. *Journal of Solid State Chemistry*, **2002**, 169, 131-138 | 3.3 | 37 |
| 120 | Structure of heavy-metal sorbed birnessite: Part 2. Results from electron diffraction. *American Mineralogist*, **2002**, 87, 1646-1661 | 2.9 | 38 |
| 119 | Structure determination of oxide compounds by electron crystallography. *Micron*, **2001**, 32, 473-9 | 2.3 | 9 |
| 118 | CaO-CuO system at high oxygen pressure: bulk synthesis and transport properties of Ca14Cu24O41. *Physica C: Superconductivity and Its Applications*, **2001**, 351, 301-307 | 1.3 | 4 |
| 117 | Crystal structure of high-Tc related NdBaCuO2BO3: TEM and neutron powder diffraction study. *Physica C: Superconductivity and Its Applications*, **2001**, 355, 119-125 | 1.3 | 4 |
| 116 | Effects of Re substitution on the structure and superconductivity of Cu1-xRexBa2YCu2Ow. *Physica C: Superconductivity and Its Applications*, **2001**, 355, 267-277 | 1.3 | 1 |
| 115 | The Fine Structure of YCuO2+x Delafossite Determined by Synchrotron Powder Diffraction and Electron Microscopy. *Journal of Solid State Chemistry*, **2001**, 156, 428-436 | 3.3 | 33 |
| 114 | Crystal Growth and Structure of AlSr2YCu2O7. *Journal of Solid State Chemistry*, **2000**, 149, 256-261 | 3.3 | 5 |

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